

JST06A-800TW

Peak gate current ($t_p=20\text{ }\mu\text{s}$, $T_j=125\text{ }^\circ\text{C}$)	I_{GM}	4	A
Average gate power dissipation ($T_j=125\text{ }^\circ\text{C}$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}		

ORDERING INFORMATION

J	ST	06	A	-800	TW
JieJie Microelectronics Co., Ltd.	Triacs	$I_T(RMS): 6A$	A: TO-220A(Ins)	800: $V_{DRM} / V_{RRM} \geq 800V$	TW: $I_{GT1-3} \leq 5mA$

MARKING

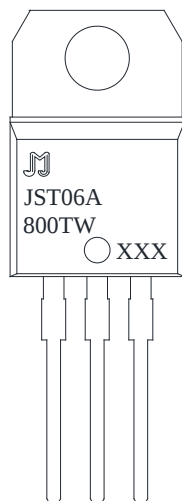


FIG.1: Maximum power dissipation versus RMS on-state current

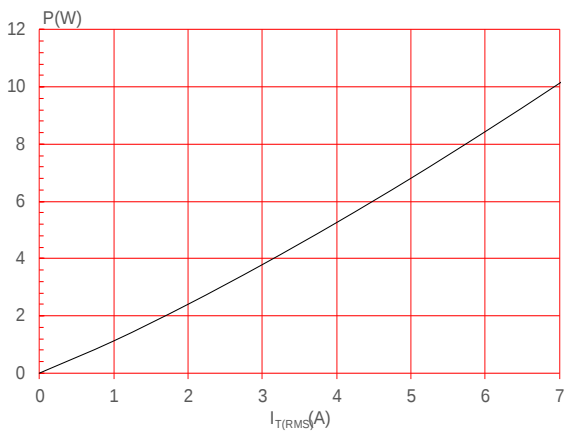
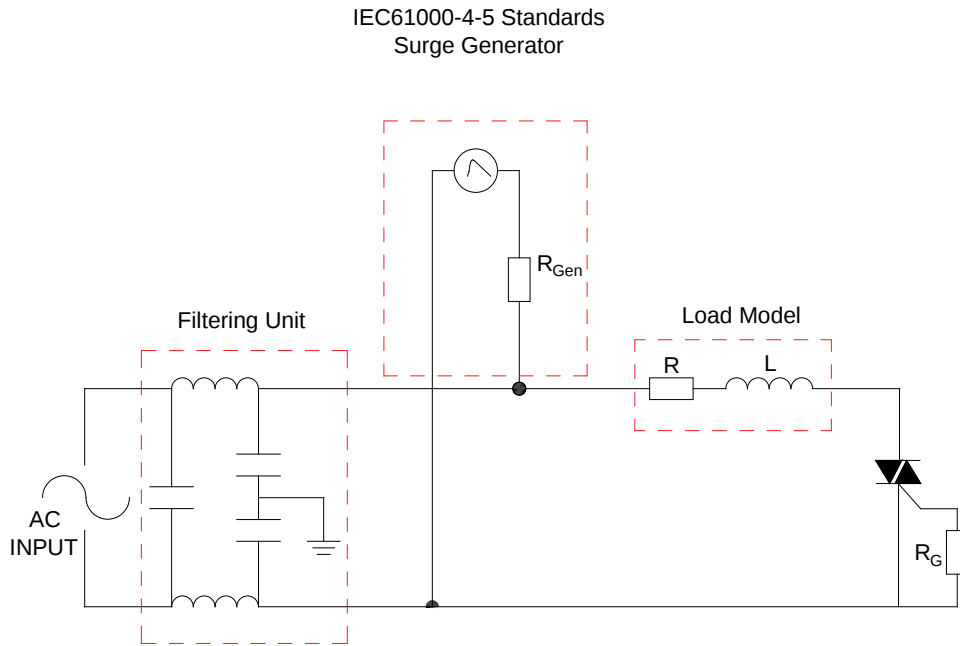


FIG.2: RMS on-state current versus case temperature



FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



ORDERING INFORMATION

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
JST06A-800TW	800	5	TO-220A(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Apr.11, 2023	A.1.0	Last updated
Oct.11, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

